Technical Data
Data Sheet N2718, REV.A

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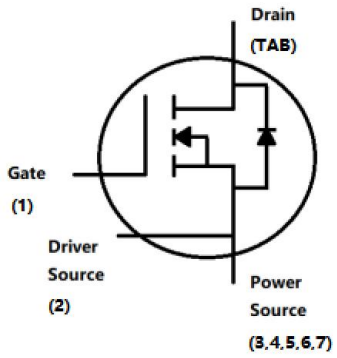
S2M0120120J
1200V SIC POWER MOSFET

V_{DS} = 1200 V
I_{DS} = 21 A
R_{DS}(on) = 133 mΩ

Description

S2M0120120J is single SiC Power MOSFET packaged in TO-263-7 case. The device is a high voltage n-channel enhancement mode MOSFET that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S2M0120120J is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- Positive temperature characteristics, easy to parallel.
- Low on-resistance Typ. RDS(on) = 133 mΩ .
- Fast switching speed and low switching losses.
- Very fast and robust intrinsic body diode.
- Process of non-bright Tin electroplatin

Applications

- EV Fast Charging Modules
- EV On Board Chargers
- Solar Inverters
- Online UPS/Industrial UPS
- SMPS (Switch Mode Power Supplies)
- DC-DC Converters
- ESS (Energy Storage Systems)

Maximum Ratings(T=25℃ unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Drain Source Voltage	V_{DSS}	V_{GS} = 0V, I_{DS} = 100uA, T_C = 25°C	1200	V
Gate Source Voltage	V_{GSS}	T_C = 25 ° C, Absolute maximum values, AC (f>1Hz)	-10 to +25	V
Gate Source Voltage	V_{GSOP}	T_C = 25°C Recommended Operational Values	-5 to +20	V
Continuous Drain Current	I_D	V_{GS} = 20V, T_C = 25°C	21	A
	I_D	V_{GS} = 20V, T_C = 100°C	15	A
Pulsed Drain Current	$I_{D,pulse}$	T_C=25˚C	66	A
Power Dissipation	P_D	T_C=25˚C	153	W

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Electrical Characteristics(T=25℃ unless otherwise specified)

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Units
Drain Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 100 uA	1200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 3.3 mA	2.0	2.9	4	V
		V_{DS} = V_{GS}, I_D = 3.3 mA, T_J = 175 °C		1.9		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V		1	100	uA
Gate Source Leakage Current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V			250	nA
Drain Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 20 V, I_D = 13.3 A		133	150	mΩ
		V_{GS} = 20 V, I_D = 13.3 A, T_J = 175 °C		212		mΩ
Transconductance	gfs	V_{DS}= 20 V, I_D= 13.3 A		5		S
		V_{DS}= 20 V, I_D= 13.3 A, T_J = 175 °C		2		S
Input Capacitance	C_{ISS}	V_{GS} = 0 V, V_{DS} = 1000 V V_{AC} = 25 mV f = 100 kHz		652		pF
Output Capacitance	C_{OSS}			47.6		
Reverse Transfer Capacitance	C_{RSS}			3.47		
C_{OSS} Stored Energy	E_{OSS}			28		uJ
Turn-On Switching Energy	E_{ON}	V_{DS} = 800 V, V_{GS} = -5/+20 V ID =13.3 A, RG(ext)=2.5 Ω		62.3		uJ
Turn-Off Switching Energy	E_{OFF}			62.7		
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 800 V, V_{GS} = -5/20 V I_D = 13.3 A, $R_{G(ext)}$= 2.5 Ω, R_L=80 Ω		3.5		ns
Rise Time	t_r			6.7		
Turn-Off Delay Time	$t_{d(off)}$			8.3		
Fall Time	t_f			10.6		
Internal Gate Resistance	$R_{G(int)}$	f = 1MHz, VAC = 25 mV, D-S short		6.4		Ω
Gate to Source Charge	Q_{gs}	V_{DS} = 800 V, V_{GS} = -5/20 V I_D = 13.3 A		12.8		nC
Gate to Drain Charge	Q_{gd}			6.0		
Total Gate Charge	Q_g			29.6		

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Reverse Diode Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Diode Forward Voltage	V_{SD}	V_{GS}= -5 V, I_{SD}= 6.7 A	3.7		V
	V_{SD}	V_{GS}= -5 V, I_{SD}= 6.7 A, T_J= 175 °C	3.3		V
Continuous Diode Forward Current	I_S	V_{GS}= -5 V, T_C= 25 ℃	20		A
Reverse Recovery Time	t_{rr}	V_{GS}= -5 V, I_{SD}= 13.3 A, T_J= 25 °C	7.3		ns
Reverse Recovery Charge	Q_{rr}	V_R= 800 V	0.05		uC
Peak Reverse Recovery Current	I_{mm}	dif/dt= 3030 A/μs	11.9		A

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.98	°C/W
Maximum Thermal Resistance Junction to Ambient	$R_{\theta JA}$		53	°C/W

Ordering Information:

Device	Package	Shipping
S2M0120120J	TO-263-7	50pcs/tube
S2M0120120JTR	TO-263-7	800pcs/reel

Marking Diagram

Where XXXXX is YYWWL

S2M = Device Type
0120 = R_{DS}(on)
120 = Reverse Voltage (1200V)
J = Package
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ratings and Characteristics Curves

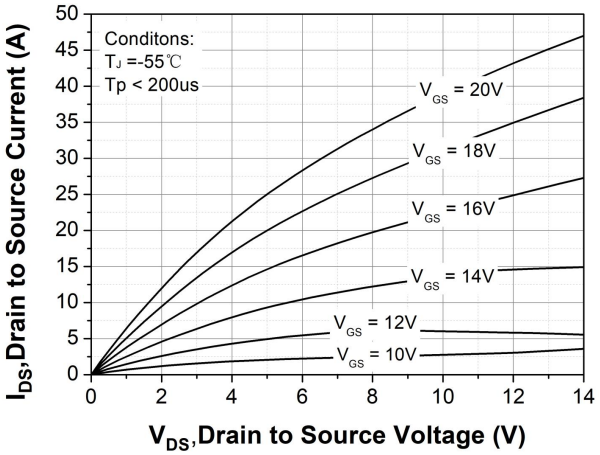

Figure 1. Output Characteristics T_J = -55 °C

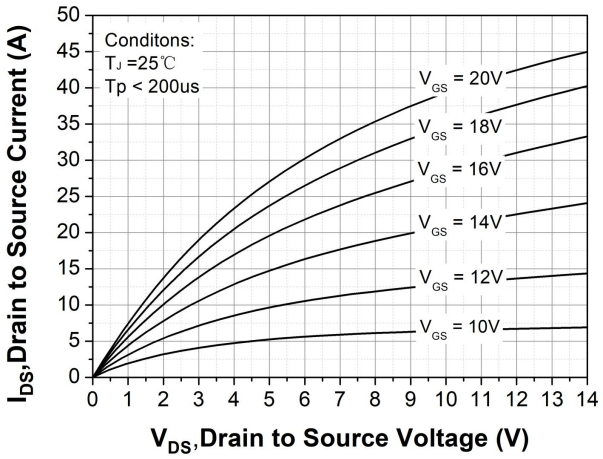

Figure 2. Output Characteristics T_J = 25 °C

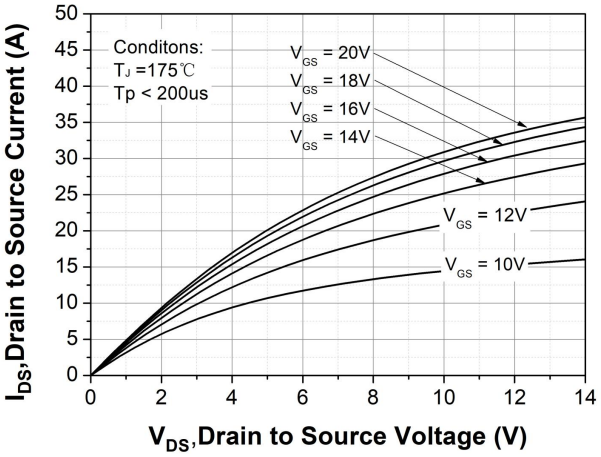

Figure 3. Output Characteristics T_J = 175°C

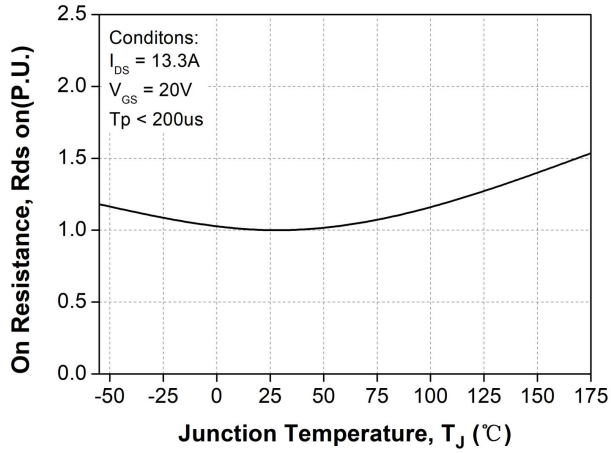

Figure 4. Normalized On-Resistance vs. Temperature

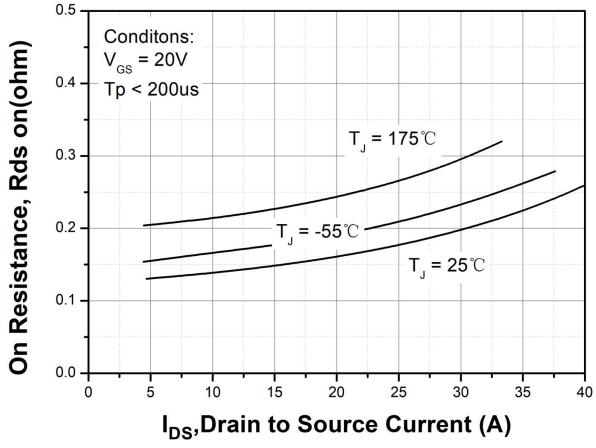

Figure 5. On-Resistance vs. Drain Current For Various Temperatures

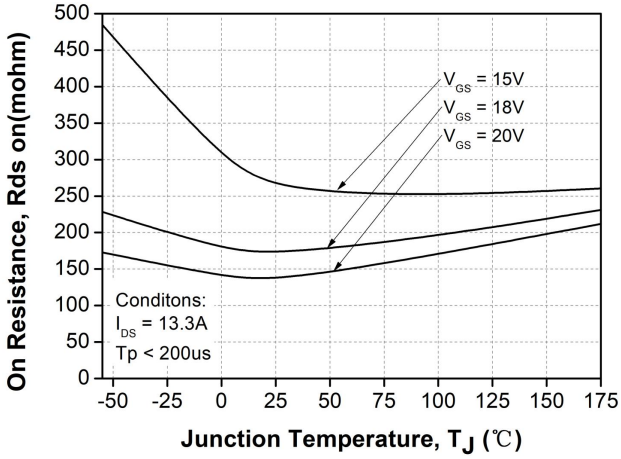

Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

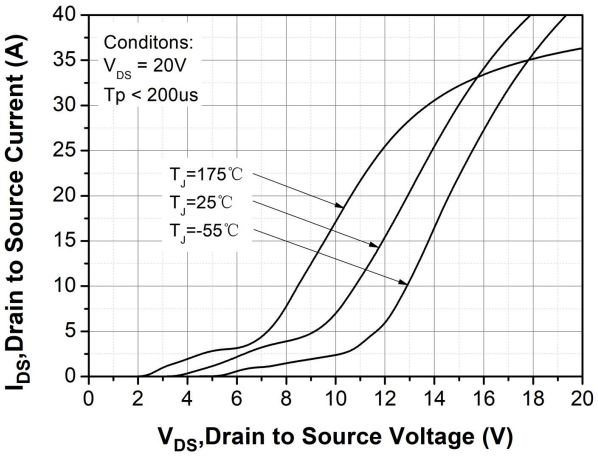

Figure 7. Transfer Characteristic for Various Junction Temperatures

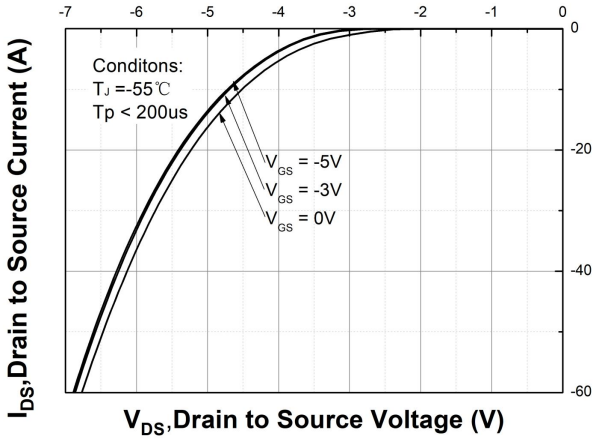

Figure 8. Body Diode Characteristic at T_J = -55 °C

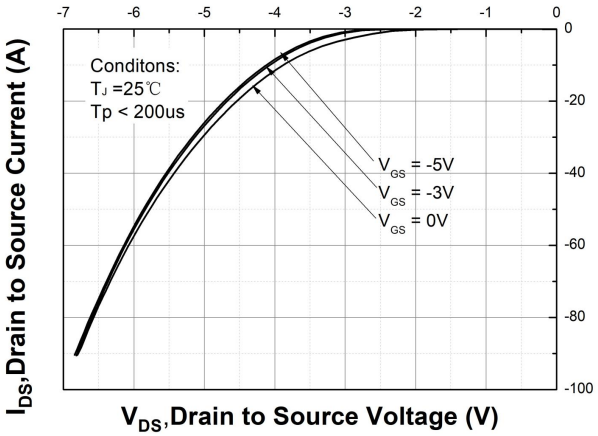

Figure 9. Body Diode Characteristic at T_J = 25 °C

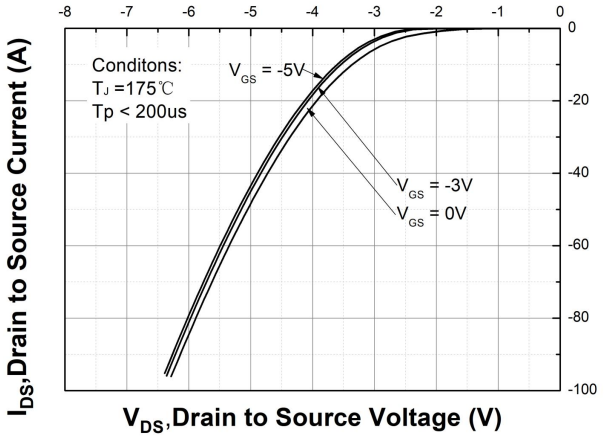

Figure 10. Body Diode Characteristic at T_J = 175 °C

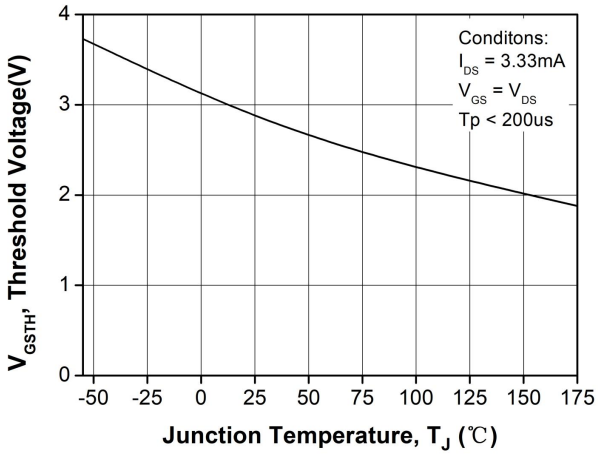

Figure 11. Threshold Voltage vs. Temperature

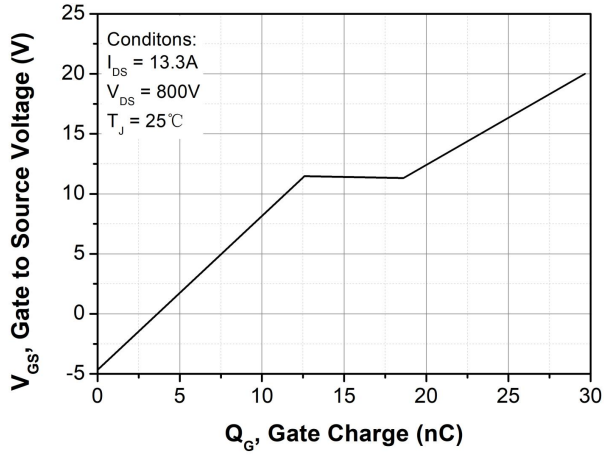

Figure 12. Gate Charge Characteristic

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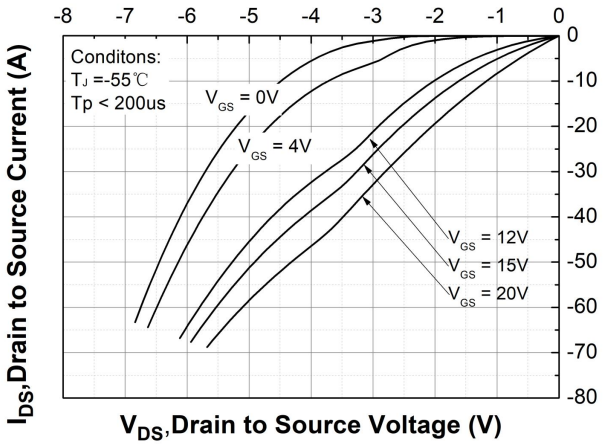

Figure 13. 3rd Quadrant Characteristic at T_J = -55 °C

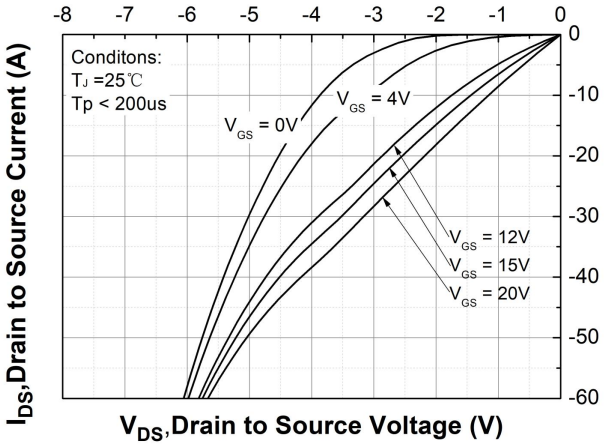

Figure 14. 3rd Quadrant Characteristic at T_J = 25 °C

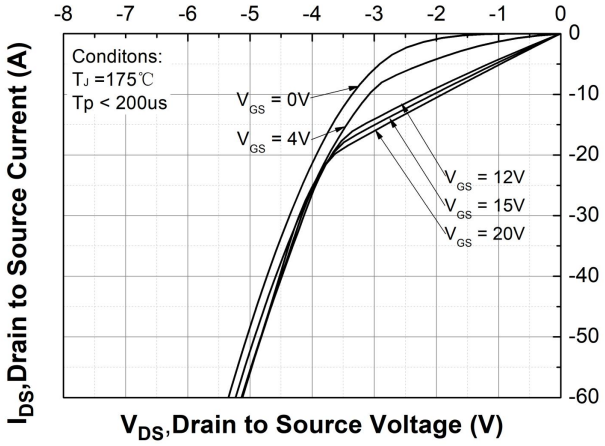

Figure 15. 3rd Quadrant Characteristic at T_J = 175°C

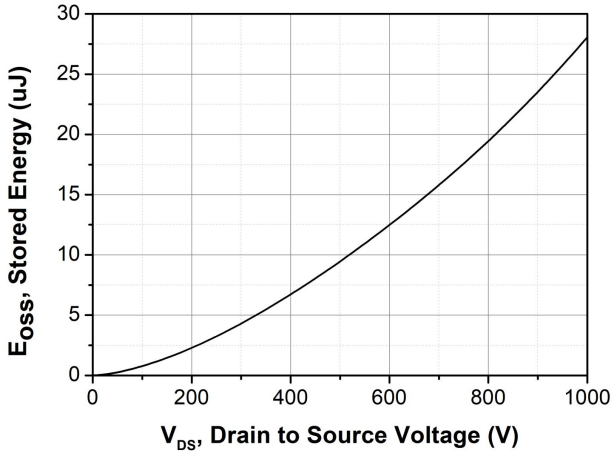

Figure 16. Output Capacitor Stored Energy

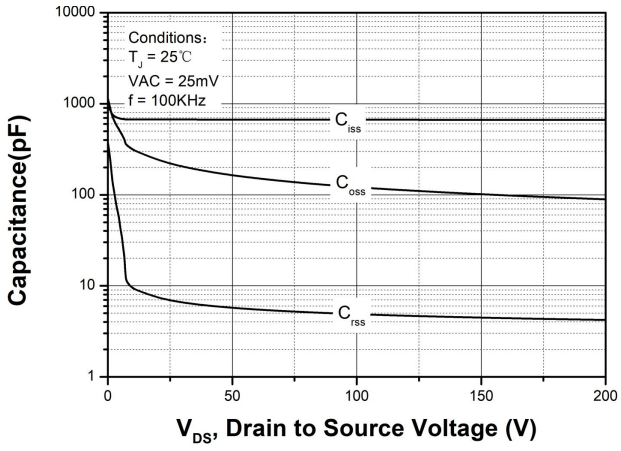

Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

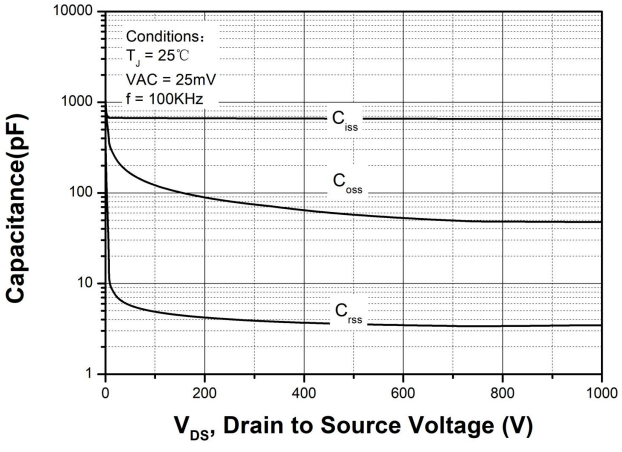

Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

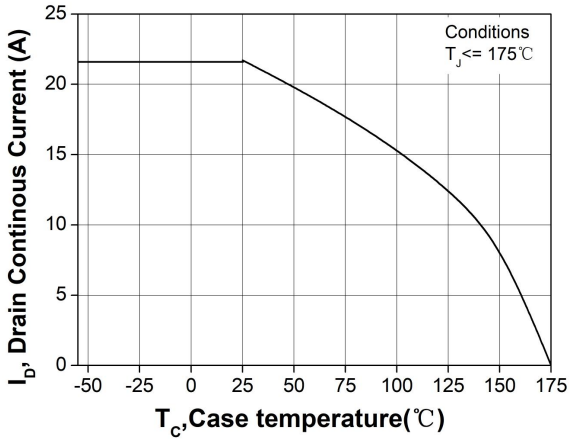

Figure 19. Continuous Drain Current Derating vs. Case Temperature

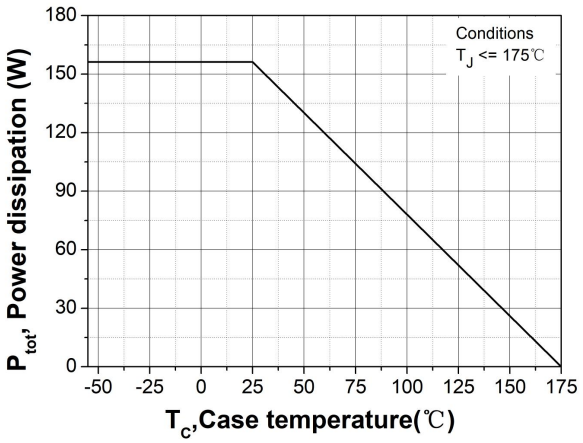

Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

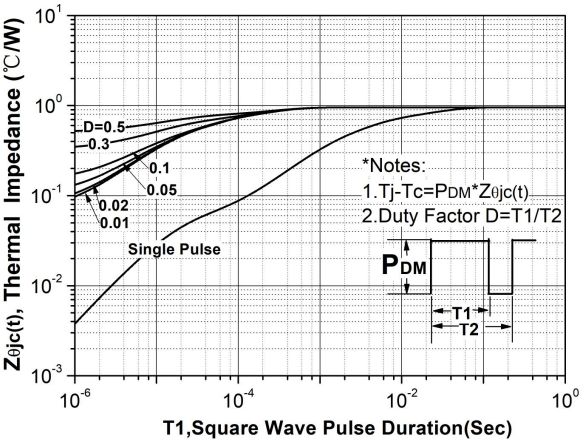

Figure 21. Transient Thermal Impedance (Junction - Case)

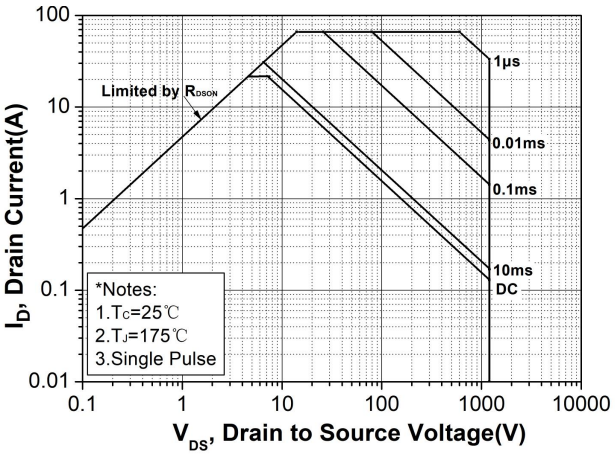

Figure 22. Safe Operating Area

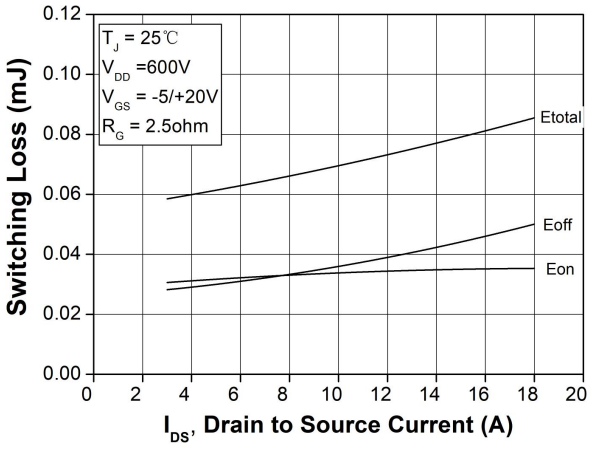

Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600V)

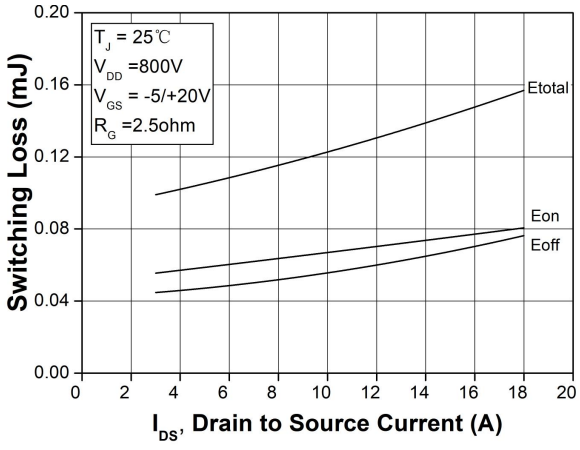

Figure 24. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 800V)

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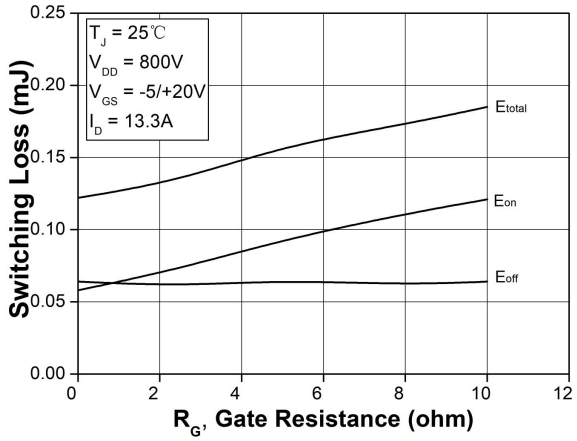


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

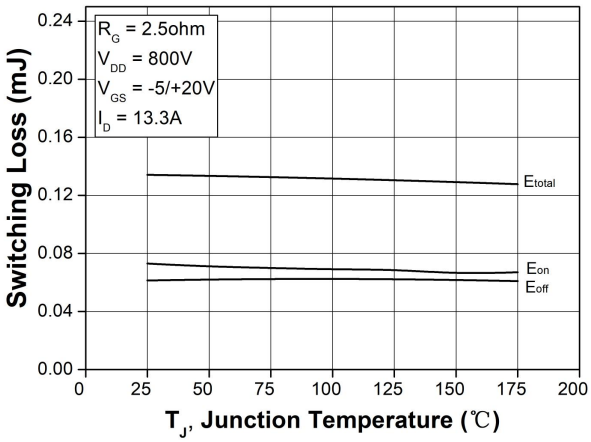


Figure 26. Clamped Inductive Switching Energy vs. Temperature

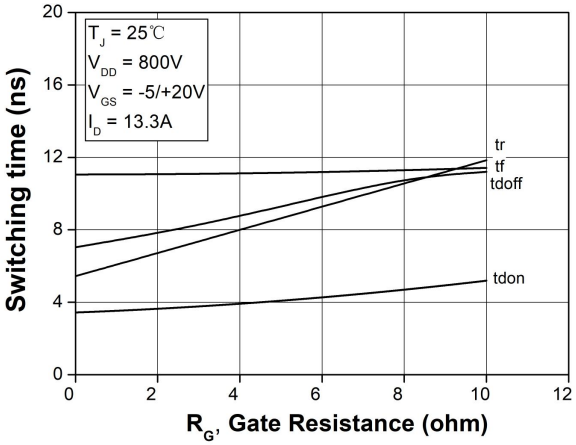


Figure 27. Switching Times vs. $R_{G(ext)}$

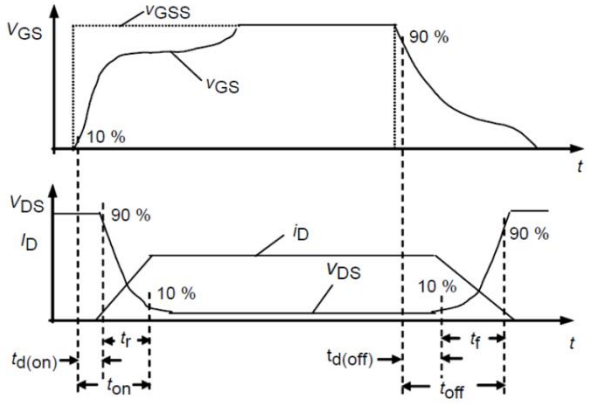
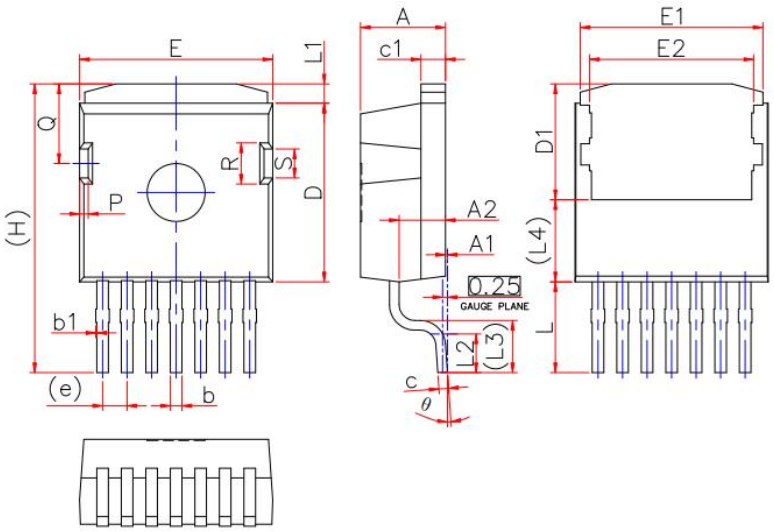


Figure 28. Switching Times Definition

Mechanical Dimensions TO-263-7



SYMBOL	Millimeters		
	TYP.	MAX.	MIN
A	4.3	4.4	4.5
A1	0	0.1	0.2
A2	2.3	2.4	2.5
b	0.5	0.6	0.7
b1	0	0.075	0.15
c	0.4	0.5	0.6
c1	1.17	1.27	1.37
D	9.05	9.25	9.45
D1	5.9	6	6.1
E	9.8	10	10.2
E1	9.36	9.46	9.56
E2	8.4	8.5	8.6
e	1.270 REF		
H	15.000 REF		
L	4.2	4.7	5.2
L1	0.7	1	1.3
L2	1.7	2	2.3
L3	2.700 REF		
L4	4.250 REF		
P	0.35	0.45	0.55
Q	4.02	4.12	4.22
R	2.03	2.13	2.23
S	1.4	1.5	1.6
θ	4°	8°	0°

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